extend from at least about 85% of the radius R of the epitaxial wafer 20 and toward the circumferential edge 315. In other embodiments, the annular edge region 302 extends from at least about 90% or at least about 95% of the radius R of the epitaxial wafer and toward the circumferential edge 315. The annular edge region 302 may terminate at the circumferential edge 315 or before the edge 315. For example, the annular edge region may extend to 99.5% of the radius R or even 99.9% of the radius R. In other embodiments, rather than imaging the wafer 20 in only an annular edge region, the entire wafer is imaged (optionally with an edge exclusion area not being imaged).

[0029] The infrared depolarization parameter of the wafer 20 may generally be any parameter based on a characterization of the wafer imaging (step 400 of FIG. 4). For example, the infrared depolarization parameter may be a wafer map (e.g., an image of the wafer showing defects, stress points, bad fraction track points or other characteristics of the scan). Alternatively or in addition, the parameter may be related to the “bad fraction” of track points (e.g., a bad fraction variability chart, a bad fraction average or the total bad fraction). Alternatively or in addition, the parameter may be related to the depolarization value (e.g., average depolarization value or total depolarization value), the depolarization contrast or the shear stress equivalent.

[0030] Once the infrared depolarization parameter is determined, suitability of the substrate for use in epitaxy may be determined. For example, the parameter may be compared to a threshold parameter and/or